

## Description

The 8T79S308 is a fully integrated signal fanout buffer for high-performance, low additive phase noise applications. The main function of the device is the distribution and fanout of high-frequency clocks or low-frequency synchronization signals.

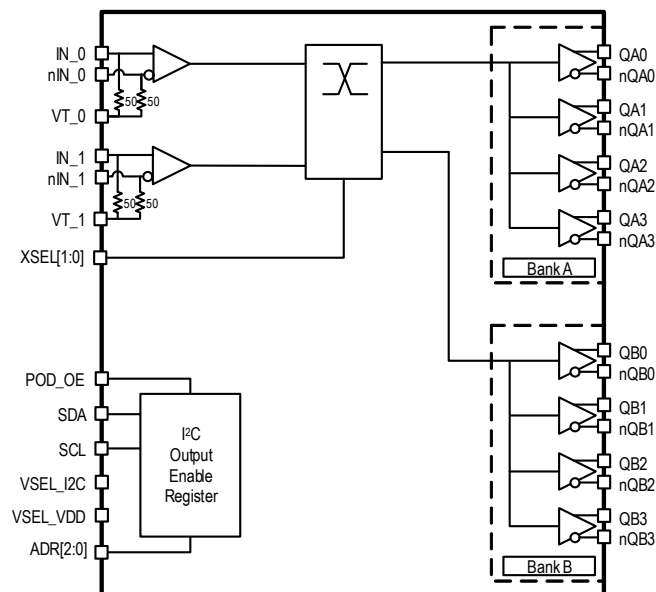
The 8T79S308 is optimized to deliver very low phase noise clocks and precise, low-skew outputs, low device-to-device skew characteristics and fast output rise/fall times help the system design to achieve deterministic clock phase relationship across devices.

The device distributes the input signals (IN\_0, IN\_1) to two fanout banks. A input select logic allows the device to operate as 1:8 buffer, dual 1:4 buffers, and to cross the input signals.

The propagation delay in both outputs banks is designed for equal delay to support fixed phase relationships between both banks. All outputs are very flexible in LVPECL/LVDS output style configuration, output signal termination, and allow both DC and AC coupling. Outputs can be individually disabled through a serial interface.

The device is packaged in a lead-free (RoHS 6) 40-VFQFPN package. The extended temperature range supports wireless infrastructure, telecommunication, and networking end equipment requirements. The 8T79S308 is a member of the high-performance clock family from IDT.

## Block Diagram



## Features

- High-performance, flexible clock/data/1PPS fanout buffer
- Low phase noise floor: -160dBc/Hz (156.256MHz clock)
- Integrated phase noise of < 65fs RMS typical (12kHz–20MHz)
- Flexible input selection
  - 1:8 Fanout modes
  - Dual 1:4 Buffer fanout modes
- Eight differential outputs, organized in two banks of four outputs
- Low-power LVPECL/LVDS outputs support DC and AC coupling and LVPECL, LVDS line terminations techniques
- Individually configured outputs through an I<sup>2</sup>C interface
  - LVPECL/LVDS output style, HCSL compatible (AC-coupled)
  - Output amplitude
  - Output enable
- Supported clock frequency range: 0 to 3GHz
- Core and output supply voltage modes:
  - 3.3V core, 3.3V, 2.5V, and 1.8V output supply
  - 2.5V core, 2.5V, and 1.8V output supply
- Selectable I<sup>2</sup>C I/O interface voltage: 1.8V and VDD
- Integrated low dropout regulators (LDOs) for excellent power supply noise rejection
- Package: 6 × 6 mm 40-VFQFPN
- Temperature range: -40°C to +105°C

## Typical Applications

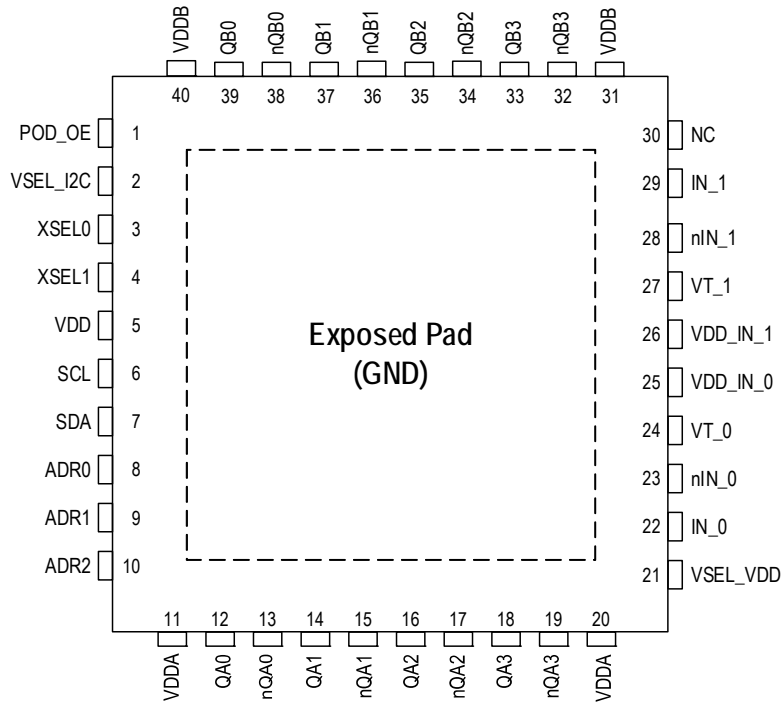
- Wireless infrastructure applications: GSM, WCDMA, LTE, LTE-A
- Ideal clock driver for jitter-sensitive ADC and DAC circuits
- Low phase noise clock generation
- Ethernet line cards
- Radar and imaging
- Instrumentation and medical

# Contents

Description .....	1
Block Diagram .....	1
Features .....	1
Typical Applications .....	1
Pin Assignments .....	3
Pin Descriptions .....	3
Principles of Operation .....	5
Overview .....	5
Voltage Supply .....	5
Pin Controlled Settings .....	6
Input Signal Selection .....	6
Configuration Registers .....	7
Device Information Registers .....	8
Device Configuration Registers .....	9
Serial Interface .....	10
I2C Interface .....	10
Absolute Maximum Ratings .....	12
Pin Characteristics .....	12
DC Characteristics .....	13
AC Characteristics .....	17
Phase Noise Plots .....	19
Application Information .....	21
Termination for Q, nQ LVDS Outputs .....	22
AC Termination for Q, nQ Outputs .....	22
Termination for Q, nQ LVPECL Outputs .....	23
Termination for Q, nQ LVPECL Outputs AC-Coupled into HCSL-Receiver .....	23
Input Interface Circuits .....	24
Thermal Characteristics .....	26
Temperature Considerations .....	26
Package Outline Drawings .....	28
Marking Diagram .....	28
Ordering Information .....	28
Glossary .....	29
Revision History .....	29

# Pin Assignments

Figure 1. Pin Assignments (Top View)



# Pin Descriptions

Table 1. Pin Descriptions<sup>[a]</sup>

Pin	Name	Type <sup>[b]</sup>	Description
<b>Signal Input Pins</b>			
22	IN_0	Input	Device clock 0 inverting and non-inverting differential clock input. Internally terminated 50Ω to VT_0. Compatible with LVPECL, LVDS signals.
23	nIN_0		
24	VT_0	Termination	Input for termination. Both IN_0 and nIN_0 inputs are internally terminated 50Ω to this pin.
29	IN_1	Input	Device clock 1 inverting and non-inverting differential clock input. Internally terminated 50Ω to VT_1. Compatible with LVPECL, LVDS signals.
28	nIN_1		
27	VT_1	Termination	Input for termination. Both IN_1 and nIN_1 inputs are internally terminated 50Ω to this pin.
<b>Signal Output Pins</b>			
12, 13	QA0, nQA0	Output	Differential clock output A0 (Bank A). Configurable LVPECL/LVDS style.
14, 15	QA1, nQA1	Output	Differential clock output A1 (Bank A). Configurable LVPECL/LVDS style.
16, 17	QA2, nQA2	Output	Differential clock output A2 (Bank A). Configurable LVPECL/LVDS style.

Table 1. Pin Descriptions<sup>[a]</sup> (Cont.)

Pin	Name	Type <sup>[b]</sup>		Description
18, 19	QA3, nQA3	Output		Differential clock output A3 (Bank A). Configurable LVPECL/LVDS style.
39, 38	QB0, nQB0	Output		Differential clock output B0 (Bank B). Configurable LVPECL/LVDS style.
37, 36	QB1, nQB1	Output		Differential clock output B1 (Bank B). Configurable LVPECL/LVDS style.
35, 34	QB2, nQB2	Output		Differential clock output B2 (Bank B). Configurable LVPECL/LVDS style.
33, 32	QB3, nQB3	Output		Differential clock output B3 (Bank B). Configurable LVPECL/LVDS style.
<b>I<sup>2</sup>C Serial Interface Pins</b>				
6	SCL	Input		Serial Control Port I <sup>2</sup> C Clock Input. Interface voltage is selected by the VSEL_I2C pin. Input has hysteresis. Use an external pull-up resistor to the serial interface supply voltage.
7	SDA	Input/ Output		Serial Control Port I <sup>2</sup> C data I/O. Interface voltage is selected by the VSEL_I2C pin. Input has hysteresis (when input). For output: open collector, use an external pull-up resistor to the selected serial interface supply voltage
<b>LVC MOS Control Function Pins</b>				
8	ADR0	Input	PD	Serial Control Port/I <sup>2</sup> C Address Bit 0, 1 and 2. LVC MOS interface levels are determined by V <sub>DD_V</sub> voltage.
9	ADR1	Input	PD	
10	ADR2	Input	PD	
3	XSEL_0	Input	PD	Signal distribution select pins 0 and 1. LVC MOS interface levels are determined by V <sub>DD_V</sub> voltage.
4	XSEL_1	Input	PD	
2	VSEL_I2C	Input	PD	Interface voltage select for the I <sup>2</sup> C interface pins. LVC MOS interface levels are determined by V <sub>DD_V</sub> voltage.
21	VSEL_VDD	Input	PD	Core supply voltage select. Set this pin to 0 or 1 according to the applied core voltage (2.5V or 3.3V) of the device. LVC MOS interface levels.
30	NC	-		No connect.
1	POD_OE	Input	PD	Power-on default output-enable state. LVC MOS interface levels are determined by V <sub>DD_V</sub> voltage.
<b>Power Pins and Exposed Pad Connection</b>				
25	VDD_IN_0	Power		Positive supply voltage (3.3V, 2.5V) for the IN_0/nIN_0 input.
26	VDD_IN_1	Power		Positive supply voltage (3.3V, 2.5V) for the IN_1/nIN_1 input.
11, 20	VDDA	Power		Positive supply voltage (3.3V, 2.5V, 1.8V) for the QA[3:0] outputs.
31, 40	VDDDB	Power		Positive supply voltage (3.3V, 2.5V, 1.8V) for the QB[3:0] outputs.
5	VDD	Power		Positive supply voltage (3.3V, 2.5V) for the device core functions.
—	GND	Power		Exposed pad: Ground supply voltage (GND) and ground return path. Connect to board GND (0V).

[a] For essential information on power supply filtering, see [Application Information](#).

[b] PU (pull-up) and PD (pull-down) indicate internal input resistors (for values, see [Figure 13](#)).

# Principles of Operation

## Overview

The 8T79S308 is designed for low phase noise and skew critical differential clock distribution systems and supports clock frequencies from 1PPS up to 3GHz. An input-to-output cross-connect, individually configurable LVPECL/LVDS outputs, amplitude settings and output enable make this device very flexible. The power-up default output enable state can be set by a dedicated control input. An I<sup>2</sup>C interface is available for individual output configurations. The signal voltage level of the I<sup>2</sup>C interface pins is configurable to 1.8V and 2.5V/3.3V voltage supply. The configurable I<sup>2</sup>C slave address pins are available to allow up to eight devices on the same I<sup>2</sup>C bus.

**Signal flow:** The device can be configured as single 1:8 or dual 1:4 buffer with selectable IN\_0 and IN\_1 inputs as signal source, controlled by the XSEL[1:0] configuration input.

The output style state of each individual differential output Q, nQ can be set by the content the I<sup>2</sup>C register 0x10 (see [Table 10](#)). A logic zero to an I<sup>2</sup>C bit in register 0x10 sets corresponding differential output to LVPECL, while a logic one sets the differential output to LVDS (see [Table 11](#)). Register 0x10 resets to logic 0 (all outputs: LVPECL) at each power-up. Setting and changing the output style through the I<sup>2</sup>C interface is asynchronous to the input reference clock.

The output amplitude of each individual differential output Q, nQ can be set by the content of the I<sup>2</sup>C registers 0x11–0x12 (see [Table 11](#)). For LVPECL outputs, the device supports amplitude settings of 500mV and 750mV; for LVDS outputs, 350mV and 500mV are supported. Register 0x11-0x12 reset to logic 0 (LVPECL standard amplitude) at each power-up. Setting and changing the output style through the I<sup>2</sup>C interface is asynchronous to the input reference clock. For LVPECL, the output termination has to be adjusted for the selected amplitude.

The output enable/disable state of each individual differential output Q, nQ can be set by the content of I<sup>2</sup>C register 0x13 (see [Table 11](#)). A logic zero to an I<sup>2</sup>C bit in register 0x02 disables the corresponding differential output in high-impedance state, while a logic one enables the differential output (see [Table 11](#)). After each power cycle, the device copies the state of the POD\_OE input into all eight bits (D7-0) of register 0x13 to: If pin POD\_OE = 0 or open, the device powers up with all outputs disabled in high-impedance state, if pin POD\_OE=1, the device powers up with all outputs enabled. After the first valid I<sup>2</sup>C write, the output enable state is controlled by the I<sup>2</sup>C register 0x13. Setting and changing the output enable state through the I<sup>2</sup>C interface is asynchronous to the input reference clock.

## Voltage Supply

Table 2. Supported Voltage Supply Operations

Core Supply $V_{DD\_V}$ [a][b]	Output Supply $V_{DD\_O}$ [c][d]
3.3V	3.3V, 2.5V, 1.8V
2.5V	2.5V, 1.8V

[a]  $V_{DD\_V}$  denominates  $V_{DD}$ ,  $V_{DD\_IN\_1}$ ,  $V_{DD\_IN\_0}$ . I<sup>2</sup>C interface levels are configured by the VSEL\_I2C pin.

[b]  $V_{DD\_V}$  core supply voltages must be equal:  $V_{DD} = V_{DD\_IN\_0} = V_{DD\_IN\_1}$ .

[c]  $V_{DD\_O}$  denominates  $V_{DDA}$  and  $V_{DDB}$ .  $V_{DD\_V} \geq V_{DD\_O}$ .

[d]  $V_{DDA} = V_{DDB}$  and  $V_{DDA} \neq V_{DDB}$  are both supported voltage operations.

## Pin Controlled Settings

Table 3. Output State Power-On Default Setting

POD_OE	Operation
0 (default)	After power-up and before the first I <sup>2</sup> C access, the outputs Qn, nQn are disabled in high impedance state.
1	After power-up and before the first I <sup>2</sup> C access, the outputs Qn, nQn are enabled.

Table 4. I<sup>2</sup>C Interface Voltage Select

VSEL_I2C	Operation
0 (default)	I <sup>2</sup> C Interface voltage (SDA, SCL) is 1.8V. The 1.8V voltage supply is regulated internally and is independent on the V <sub>DD_V</sub> voltage.
1	I <sup>2</sup> C Interface voltage (SDA, SCL) is equal to the voltage supplied to V <sub>DD_V</sub> (2.5V or 3.3V).

Table 5. Core Voltage Supply Select

VSEL_VDD	Operation
0 (default)	V <sub>DD_V</sub> core voltage is 2.5V.
1	V <sub>DD_V</sub> core voltage is 3.3V.

## Input Signal Selection

Table 6. Input Signal and Buffer Signal Flow Selection

XSEL_1	XSEL_0	Signal Flow	Description
0 (default)	0 (default)	IN_0 → QA0-3 and QB0-3	1:8 Buffer
0	1	IN_0 → QA0-3 IN_1 → QB0-3	Dual 1:4 Buffer
1	0	IN_0 → QB0-3 IN_1 → QA0-3	Dual 1:4 Buffer, crossed signals
1	1	IN_1 → QA0-3 and QB0-3	1:8 Buffer (from IN_1)

## Configuration Registers

Table 7. Configuration Registers

Register Address	Register Description
0x00-0x02	Reserved
0x03	Device Type
0x04	Device ID
0x05	Device ID
0x06	Device Version
0x07-0x0B	Reserved
0x0C	Vendor ID
0x0D	Vendor ID
0x0E	I <sup>2</sup> C Address
0x0F	Reserved
0x10	Output Style
0x11	Output Amplitude
0x12	Output Amplitude
0x13	Output Enable
0x14-0x1F	Reserved

## Device Information Registers

Table 8. Device Information Bit Field Locations

Bit Field Location								
Register Address	D7	D6	D5	D4	D3	D2	D1	D0
0x03								DEV_TYPE[7:0]
0x04								DEV_ID[7:0]
0x05								DEV_ID[15:8]
0x06								DEV_VER[7:0]
0x0C								VENDOR_ID[7:0]
0x0D								VENDOR_ID[15:8]
0x0E	Reserved							I2C_ADR

Table 9. Device Information Register Descriptions

Register Description			
Bit Field Name	Field Type	Default (Binary)	Description
DEV_TYPE[7:0]	R only	0x07	Device (Chip) Type Reads 0x07 (RF-Buffer) after power-up and reset.
DEV_ID[15:0]	R only	0x04: 0100 0011 0x05: 0000 0000  Value: 0x0043	Device ID Device is composed of registers 0x05 (high byte) and register 0x04 (low byte). Reads 0x0043 after power-up and reset.
DEV_VER[7:0]	R only	0x00  Value: 0x00	Device Version 0x00. Reads 0x00 (First silicon revision) after power-up and reset.
VENDOR_ID	R only	0x0C: 0010 0110 0x0D: 0000 0100  Value: 0x0426	Vendor ID 0x0426 (Integrated Device Technology, IDT). Reads 0x0426 (IDT) after power-up and reset.



Table 9. Device Information Register Descriptions

Register Description			
Bit Field Name	Field Type	Default (Binary)	Description
I2C_ADR[6:0]	R	1101 [ADR2] [ADR1] [ADR0]	<p>I<sup>2</sup>C Device address</p> <p>This read-only register stores the binary I<sup>2</sup>C device address: 1101[ADR2][ADR1][ADR0].</p> <p>Bit D2 is equal to the logic state of the ADR2 pin</p> <p>Bit D1 is equal to the logic state of the ADR1 pin</p> <p>Bit D0 is equal to the logic state of the ADR0 pin.</p> <p>This register cannot be used to change the device address.</p>

## Device Configuration Registers

Table 10. Device Configuration Bit Field Locations

Bit Field Location								
Register Address	D7	D6	D5	D4	D3	D2	D1	D0
0x10	STYLE_QB 3	STYLE_QB 2	STYLE_QB 1	STYLE_QB 0	STYLE_QA 3	STYLE_QA 2	STYLE_QA 1	STYLE_QA 0
0x11	A_QB3		A_QB2		A_QB1		A_QB0	
0x12	A_QA3		A_QA2		A_QA1		A_QA0	
0x13	OE_QB3	OE_QB2	OE_QB1	OE_QB0	OE_QA3	OE_QA2	OE_QA1	OE_QA0

Table 11. Device Configuration Register Descriptions

Register Description			
Bit Field Name	Field Type	Default (Binary)	Description
STYLE_Qn	R/W	0	<p>0 = Output is LVPECL.</p> <p>1 = Output is LVDS.</p>

Table 11. Device Configuration Register Descriptions

Register Description					
Bit Field Name	Field Type	Default (Binary)	Description		
A_Qn	R/W	00	Output Amplitude		
			A_Qn[1:0]	Amplitude if Output is LVPECL	Amplitude if Output is LVDS
			00	750mV (standard LVPECL) Output termination: see <a href="#">Figure</a>	500mV amplitude (high-amplitude LVDS) Output termination: 100Ω between Q, nQ; see <a href="#">Figure 7</a> , <a href="#">Figure 8</a> , <a href="#">Figure 9</a> .
			01	500mV (low-amplitude LVPECL) Output termination: see <a href="#">Figure</a>	
			10	Reserved	350mV amplitude (standard LVDS) Output termination: 100Ω between Q, nQ; see <a href="#">Figure 7</a> , <a href="#">Figure 8</a> , <a href="#">Figure 9</a> .
			11	Reserved	Reserved
			V <sub>DD_O</sub> = 1.8V: output amplitudes of 350mV and 500mV are available, 750mV is not available.		
OE_Qn	R/W	POD_OE pin state	<p>Output Enable</p> <p>0 = Output Qn, nQn is disabled in the high-impedance state.</p> <p>1 = Output Qn, nQn is enabled.</p> <p>After each power cycle, the device copies the state of the POD_OE input to all eight bits (D7-0) of this register. If pin POD_OE = 1 or open, the device powers up with all outputs enabled, if pin POD_OE=0, the device powers up with all outputs disabled in high-impedance state. After the first valid I<sup>2</sup>C write, the output enable state is controlled by this register.</p>		

## Serial Interface

The 8T79S308 supports an I<sup>2</sup>C configuration interface.

## I<sup>2</sup>C Interface

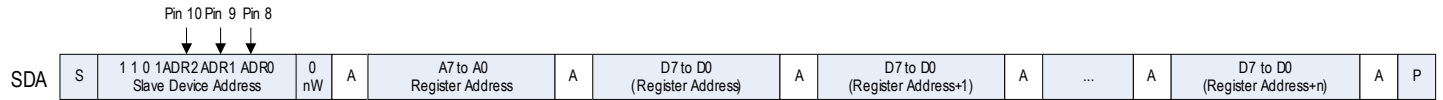
The device will respond as a slave in an I<sup>2</sup>C compatible configuration at a base address of 1101[ADR2, ADR1, ADR0]b, to allow access to any of the internal registers for device programming or examination of internal status. The ADR[2:0] bits of the I<sup>2</sup>C interface address are set by the logic state of the ADR2 (pin 10), ADR1 (pin 9) and ADR0 (pin 8) inputs. If more than one 8T79S308 device is connected to the same I<sup>2</sup>C bus, set ADR[2:0] to different states on each device to avoid address conflicts.

The I<sup>2</sup>C interface is designed to fully support v1.2 of the I<sup>2</sup>C Specification for Normal and Fast mode operation. The device acts as a slave device on the I<sup>2</sup>C bus at 100kHz or 400kHz using a fixed base address of 1101[ADR2, ADR1, ADR0]b. The interface accepts byte-oriented block write and block read operations. One address byte specifies the register address of the byte position of the first register to write or read. Data bytes (registers) are accessed in sequential order from the lowest to the highest byte (most significant bit first). Read and write block transfers can be stopped after any complete byte transfer. During a write operation, data is moved into the registers byte by byte and before a STOP bit is received.

The device implements registers in the address range 0x00 to 0x1F. Write access to the address range 0x20-0xFF has no effect, read access to this range will return 0x00.

For full electrical I<sup>2</sup>C compliance, it is recommended to use external pull-up resistors for SDA and SCL. The internal pull-up resistors have a size of 51kΩ typical.

Figure 2. I<sup>2</sup>C Write Data (Master Transmit, Slave Receive) from any Register Address



Write to slave to the specified register address A [7:0]. The slave auto -increments the register address and data is written sequentially .

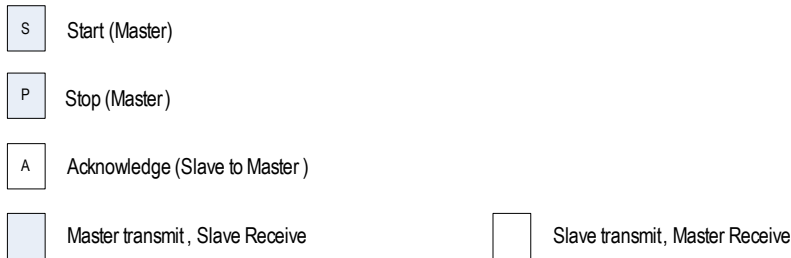
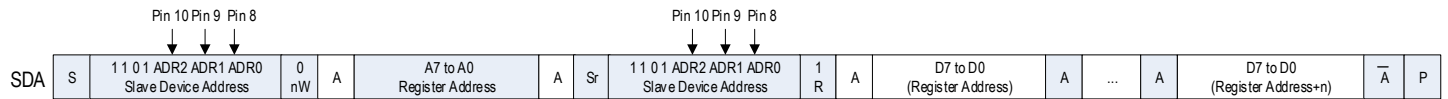
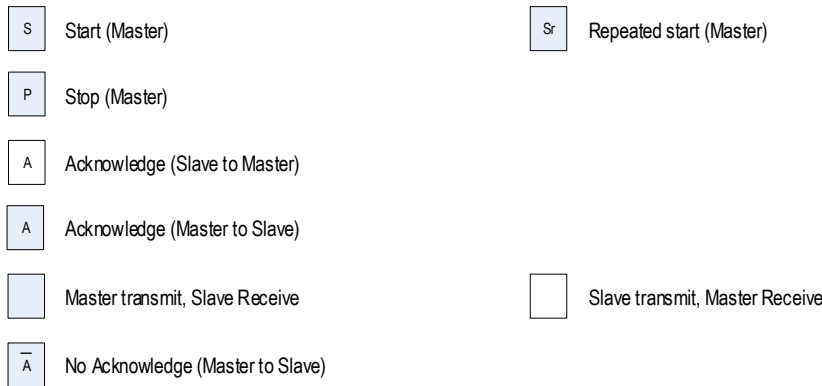


Figure 3. I<sup>2</sup>C Read Data (Slave Transmit, Master Receive) from any Register Address



Read from slave from the specified register address A[7:0]. Data is transmitted to the master after a change of the transfer direction with a repeated start. The slave auto-increments the register address and transmits register data to the master sequentially.



## Absolute Maximum Ratings

The absolute maximum ratings are stress ratings only. Stresses greater than those listed below can cause permanent damage to the device. Functional operation of the 8T79S308 at absolute maximum ratings is not implied. Exposure to absolute maximum rating conditions may affect device reliability.

Table 12. Absolute Maximum Ratings

Item	Rating
Supply Voltage, $V_{DD\_V}$ , $V_{DD\_O}$	3.6V
Inputs	-0.5V to $V_{DD\_V} + 0.5V$
Outputs, $V_O$ (SDA)	-0.5V to $V_{DD\_O} + 0.5V$
Outputs, $I_O$ (LVPECL) Continuous Current Surge Current	50mA 100mA
Outputs, $I_O$ (LVDS) Continuous Current Surge Current	50mA 100mA
Input termination current, $I_{VT}$	$\pm 35mA$
Operating Junction Temperature, $T_J$	125°C
Storage Temperature, $T_{STG}$	-65°C to 150°C
ESD - Human Body Model <sup>[a]</sup>	2000V
ESD - Charged Device Model <sup>[a]</sup>	500V

[a] According to JEDEC JS-001-2012/JESD22-C101

## Pin Characteristics

Table 13. Pin Characteristics,  $V_{DD\_V} = (3.3V \text{ or } 2.5V) \pm 5\%$ ,  $V_{DD\_O} = (3.3V \text{ or } 2.5V \text{ or } 1.8V) \pm 5\%$ ,  $T_A = -40^\circ C \text{ to } +105^\circ C$  (Case)

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$C_{IN}$ <sup>[a]</sup>	Input Capacitance	IN_0, nIN_0, IN_1, nIN_1.		2	4	pF
		Other inputs.		2	4	pF
$R_{PD}$	Input Pull-Down Resistor			51		k $\Omega$
$R_T$	Input Termination Impedance	IN_0, nIN_0 to VT_0.		50		$\Omega$
		IN_1, nIN_1 to VT_1.		50		

[a] Guaranteed by design.

## DC Characteristics

Table 14. Power Supply DC Characteristics,  $V_{DD\_V} = (3.3V \text{ or } 2.5V) \pm 5\%$ ,  $V_{DD\_O} = (3.3V \text{ or } 2.5V \text{ or } 1.8V) \pm 5\%$ ,  $T_A = -40^\circ\text{C to } +105^\circ\text{C}$  (Case)<sup>[a][b]</sup>

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$V_{DD\_V}$	Core Supply Voltage		2.5 - 5% 3.3 - 5%	2.5 3.3	2.5 + 5% 3.3 + 5%	V
$V_{DD\_O}$	Output Supply Voltage		2.5 - 5% 3.3 - 5% 1.8 - 5%	2.5 3.3 1.8	2.5 + 5% 3.3 + 5% 1.8 + 5%	V
$I_{DD\_V} + I_{DD\_O}$	Total Power Supply Current	$V_{DD\_V} = V_{DD\_O} = 2.5V.$		395	457	mA
		$V_{DD\_V} = V_{DD\_O} = 3.3V.$		406	467	
		$V_{DD\_V} = 2.5V, V_{DD\_O} = 1.8V.$		345	395	

[a] Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

[b]  $V_{DD\_V} \geq V_{DD\_O}$

Table 15. Typical Power Supply DC Current Characteristics,  $V_{DD\_V} = 3.3V$ ,  $V_{DD\_O} = 3.3V$ ,  $T_A = 25^\circ\text{C}$ <sup>[a][b]</sup>

Symbol	Supply Pin Current		Test Case				Unit
			1	2	3	4	
Qn	Style		LVPECL	LVPECL	LVDS	LVDS	
	State		On	On	On	On	
	Amplitude		500	750	350	500	mV
$I_{DD\_CA}$	Current through VDD pin		4	4	4	4	mA
$I_{DD\_CB}$	Current through VDDA pin		135	160	108	112	mA
$I_{DD\_CC}$	Current through VDDB pin		135	160	108	112	mA
$I_{DD\_CD}$	Current through VDD_IN_0 pin		41	41	40	40	mA
$I_{DD\_CE}$	Current through VDD_IN_1 pin		41	41	40	40	mA
$P_{TOT}$	Total Device Power Consumption		0.709	0.805	0.99	1.02	W
$P_{TOT, SYS}$	Total System Power Consumption <sup>[c]</sup>		1.18	1.34	0.99	1.02	W

[a] Configuration:  $f_{CLK}$  (input) = 245.76MHz, Qn outputs terminated according to amplitude settings.

[b] Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

[c] Includes total device power consumption and the power dissipated in external output termination components.

Table 16. Typical Power Supply DC Current Characteristics,  $V_{DD_V} = 2.5V$ ,  $V_{DD_O} = 2.5V$ ,  $T_A = 25^\circ C$ <sup>[a][b]</sup>

Symbol	Supply Pin Current		Test Case				Unit
			1	2	3	4	
	Qn	Style	LVPECL	LVPECL	LVDS	LVDS	
		State	On	On	On	On	
		Amplitude	500	750	350	500	mV
$I_{DD\_CA}$	Current through VDD pin		4	4	4	4	mA
$I_{DD\_CB}$	Current through VDDA pin		131	156	107	111	mA
$I_{DD\_CC}$	Current through VDDDB pin		131	156	107	111	mA
$I_{DD\_CD}$	Current through VDD_IN_0 pin		40	40	39	39	mA
$I_{DD\_CE}$	Current through VDD_IN_1 pin		40	40	39	39	mA
$P_{TOT}$	Total Device Power Consumption		0.587	0.672	0.98	1.00	W
$P_{TOT\_SYS}$	Total System Power Consumption <sup>[c]</sup>		1.15	1.31	0.98	1.00	W

[a] Configuration:  $f_{CLK}$  (input) = 245.76MHz, Qn outputs terminated according to amplitude settings.

[b] Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500lfpm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

[c] Includes total device power consumption and the power dissipated in external output termination components.

Table 17. LVCMOS Input DC Characteristics,  $V_{DD_V} = (3.3V \text{ or } 2.5V) \pm 5\%$ ,  $V_{DD_O} = (3.3V \text{ or } 2.5V \text{ or } 1.8V) \pm 5\%$ ,  $T_A = -40^\circ C \text{ to } +105^\circ C$  (Case)<sup>[a][b]</sup>

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
$V_{IH}$	Input High Voltage		$V_{DD_V} = 2.5V$ .	1.7		$V_{DD_V}$	V
			$V_{DD_V} = 3.3V$ .	2		$V_{DD_V}$	V
$V_{IL}$	Input Low Voltage			-0.3		0.5	V
$I_{IH}$	Input High Current	Input with pull-down resistor	$V_{DD_V} = 2.5V \text{ or } 3.3V$ . $V_{IN} = V_{DD_V}$			150	$\mu A$
$I_{IL}$	Input Low Current		$V_{DD_V} = 2.5V \text{ or } 3.3V$ . $V_{IN} = 0V$ .	-5			$\mu A$

[a] Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfpm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

[b] LVCMOS inputs: ADR[2:0], XSEL[1:0], VSEL\_VDD, VSEL\_I2C, and POD\_OE.

Table 18. I<sup>2</sup>C Input/Output DC Characteristics,  $V_{DD_V} = (3.3V \text{ or } 2.5V) \pm 5\%$ ,  $V_{DD_O} = (3.3V \text{ or } 2.5V \text{ or } 1.8V) \pm 5\%$ ,  $T_A = -40^\circ\text{C to } +105^\circ\text{C}$  (Case)<sup>[a][b]</sup>

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
$V_I$	Input Voltage			-0.3		3.3V	V
$V_{T+}$	Positive-going input threshold voltage		VSEL_I2C = 0. VSEL_I2C = 1, $V_{DD_V} = 2.5V$ . VSEL_I2C = 1, $V_{DD_V} = 3.3V$ .	0.660	1.10–1.40 1.45–1.75	1.365	V
$V_{T-}$	Negative-going input threshold voltage		VSEL_I2C = 0. VSEL_I2C = 1, $V_{DD_V} = 2.5V$ . VSEL_I2C = 1, $V_{DD_V} = 3.3V$ .	0.495	0.91 0.65–0.95 0.8–1.1	1.170	V
$V_H$	Hysteresis Voltage	$V_{T+} - V_{T-}$	VSEL_I2C = 0. VSEL_I2C = 1, $V_{DD_V} = 2.5V$ . VSEL_I2C = 1, $V_{DD_V} = 3.3V$ .	0.165	0.6 0.15–0.45 0.5–0.8	0.780	V
$I_{IH}$	Input High Current		$V_{DD_V} = 2.5V \text{ or } 3.3V$ . $V_{IN} = V_{DD_V}$			150	$\mu\text{A}$
$I_{IL}$	Input Low Current		$V_{DD_V} = 2.5V \text{ or } 3.3V$ . $V_{IN} = 0V$ .	-5			$\mu\text{A}$
$V_{OL}$	Output Low Voltage		VSEL_I2C = 0, $I_{OL} = 4\text{mA}$ . VSEL_I2C = 1, $I_{OL} = 4\text{mA}$ .		0.292 0.292	0.55	V

[a] Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfpm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

[b] Valid for inputs/outputs: SCL and SDA. Inputs have hysteresis and tolerate any voltage up to 3.3V.

Table 19. Differential Input DC Characteristics,  $V_{DD_V} = (3.3V \text{ or } 2.5V) \pm 5\%$ ,  $V_{DD_O} = (3.3V \text{ or } 2.5V \text{ or } 1.8V) \pm 5\%$ ,  $T_A = -40^\circ\text{C to } +105^\circ\text{C}$  (Case)<sup>[a]</sup>

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
$V_{IN}$	Input Voltage Swing	IN_0, IN_1		0.15		1.2	V
$V_{DIFF\_IN}$	Differential Input Voltage Swing			0.3		2.4	V
$V_{CMR}$	Common Mode Input Voltage			1		$V_{DD_V} - (V_{IN}/2)$	V
$R_T$	Input Termination Impedance		IN_0, nIN_0 to VT_0, IN_1, nIN_1 to VT_1.	40	50	60	$\Omega$
$R_{T\_DIFF}$	Differential Input Termination Impedance		IN_0 to nIN_0. IN_0 to nIN_1.	80	100	120	$\Omega$

[a] Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

Table 20. LVPECL DC Characteristics (QAn, QBn),  $V_{DD_V} = (3.3V \text{ or } 2.5V) \pm 5\%$ ,  $V_{DD_O} = (3.3V \text{ or } 2.5V \text{ or } 1.8V) \pm 5\%$ ,  $T_A = -40^\circ\text{C to } +105^\circ\text{C}$  (Case)

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$V_{OH}$	Output High Voltage	Amplitude = 750mV. Amplitude = 500 mV.	$V_{DD_O} - 1.04$ $V_{DD_O} - 0.99$	$V_{DD_O} - 0.9$ $V_{DD_O} - 0.89$	$V_{DD_O} - 0.83$ $V_{DD_O} - 0.82$	V
$V_{OL}$	Output Low Voltage	Amplitude = 750mV. Amplitude = 500 mV.	$V_{DD_O} - 1.73$ $V_{DD_O} - 1.48$	$V_{DD_O} - 1.62$ $V_{DD_O} - 1.38$	$V_{DD_O} - 1.56$ $V_{DD_O} - 1.33$	V

Table 21. LVDS DC Characteristics (QAn, QBn),  $V_{DD_V} = (3.3V \text{ or } 2.5V) \pm 5\%$ ,  $V_{DD_O} = (3.3V \text{ or } 2.5V \text{ or } 1.8V) \pm 5\%$ ,  $T_A = -40^\circ\text{C to } +105^\circ\text{C}$  (Case)<sup>[a]</sup>

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
$V_{OS}$	Offset Voltage <sup>[b]</sup>	$V_{DD_O} = 3.3V$	500mV Amplitude. 350mV Amplitude.	1.8 1.9	2.3 2.3	2.8 2.9	V
$V_{OS}$	Offset Voltage <sup>[c]</sup>	$V_{DD_O} = 2.5V$	500mV Amplitude. 350mV Amplitude.	1.05 1.10	1.42 1.42	1.75 1.80	V
$V_{OS}$	Offset Voltage <sup>[d]</sup>	$V_{DD_O} = 1.8V$	500mV Amplitude. 350mV Amplitude.	0.40 0.45	0.70 0.78	1.0 1.1	V
$\Delta V_{OS}$	V <sub>OS</sub> Magnitude Change				10	50	mV

[a] Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

[b]  $V_{OS}$  changes with  $V_{DD_O}$ .

[c]  $V_{OS}$  changes with  $V_{DD_O}$ .

[d]  $V_{OS}$  changes with  $V_{DD_O}$ .



## AC Characteristics

Table 22. AC Characteristics,  $V_{DD_V} = (3.3V \text{ or } 2.5V) \pm 5\%$ ,  $V_{DD_O} = (3.3V \text{ or } 2.5V \text{ or } 1.8V) \pm 5\%$ ,  $T_A = -40^\circ\text{C to } +105^\circ\text{C}$  (Case)<sup>[a]</sup>

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
$f_{IN}$	Signal Input and Output Frequency			0		3000	MHz
$f_{SCL}$	I <sup>2</sup> C Clock Frequency					400	kHz
$V_{IN}$	Input Voltage Amplitude <sup>[b]</sup>	IN <sub>n</sub>		0.15		1.2	V
$V_{DIFF\_IN}$	Differential Input Voltage Amplitude <sup>[b][c]</sup>	IN <sub>n</sub>		0.3		2.4	V
$V_{CMR}$	Common Mode Input Voltage			1.0		$V_{DD_V} - (V_{IN}/2)$	V
odc	Output Duty Cycle		QAn, QBn (Clock)	45	50	55	%
			QAn, QBn (Clock) > 2.5GHz	40	50	60	
$t_R / t_F$	Output Rise/Fall Time, Differential		QAn, QBn (Clock), 20% to 80%.		100	200	ps
			QAn, QBn, 20% to 80%.		100	200	ps
$V_{O(PP)}$	LVPECL Output Voltage Swing, Peak-to-peak	750mV	1GHz.	630	730	830	mV
		750mV	2GHz.	640	744	850	mV
	LVPECL Differential Output Voltage Swing, Peak-to-peak	750mV	1GHz.	1260	1460	1660	mV
		750mV	2GHz.	1280	1488	1700	mV
$V_{OD}$	LVDS Output Voltage Swing, Peak-to-peak	350mV	1GHz.	280	360	420	mV
		350mV	2GHz.	230	360	470	mV
$V_{OD}$	LVDS Differential Output Voltage Swing, Peak-to-peak	350mV	1GHz.	560	720	840	mV
		350mV	2GHz.	460	720	940	mV
$t_{PD}$	Propagation delay between any signal input and any QAn, QBn output					750	ps
$t_{PDZ}$	Output enable and disable time		From active state to disable <sup>[d]</sup>		1	3	$\mu\text{s}$
			From disable to active state <sup>[e]</sup>		30	50	
$t_{sk(o)}$	Output Skew <sup>[f][g]</sup>		Within one output bank.		10	25	ps
			Any output.		16	35	ps
$t_{sk(pp)}$	Part-to-part Skew <sup>[f][g]</sup>					200	ps
$t_{sk(p)}$	Output Pulse Skew <sup>[g]</sup>		Any output.		21	50	ps
$L(\infty)$	Output Noise Floor		QAn, QBn, 156.25MHz. LVDS Outputs		-160	-155	dBc
			QAn, QBn, 156.25MHz. LVPECL Outputs		-160	-157	

Table 22. AC Characteristics,  $V_{DD\_V} = (3.3V \text{ or } 2.5V) \pm 5\%$ ,  $V_{DD\_O} = (3.3V \text{ or } 2.5V \text{ or } 1.8V) \pm 5\%$ ,  $T_A = -40^\circ\text{C to } +105^\circ\text{C (Case)}^{[a]}$  (Cont.)

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
L	Additive Phase Noise, RMS	QAn, QBn, 156.25MHz (12kHz–20MHz).		60	100	fs
		QAn, QBn, 245.76MHz (12kHz–20MHz).		50	80	fs
		QAn, QBn, 245.76MHz (1kHz–61.44MHz).		95	110	fs
$\Delta F$	Output isolation between any neighboring clock output	$f_{OUT} = 125\text{MHz}$ .		80	75	dB
		$f_{OUT} = 245.76\text{MHz}$ .		75	70	dB
$\Delta F$	Input isolation between any signal input	$f_{IN} = 125\text{MHz}$ .		80	75	dB
		$f_{IN} = 245.76\text{MHz}$ .		75	70	dB
CMNR	Common mode noise rejection <sup>[h]</sup>	$f_{IN} = 156.25\text{MHz}$ .		-90		dBc

[a] Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfpm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

[b]  $V_{IL}$  should not be less than  $-0.3V$  and  $V_{IH}$  should not be greater than  $V_{DD\_V}$ .

[c] Common Mode Input Voltage is defined as the cross-point voltage.

[d] Measured from I<sup>2</sup>C slave acknowledge bit to output in high-impedance state. Verified by simulation.

[e] Measured from I<sup>2</sup>C slave acknowledge bit to output in active low/high state. Verified by simulation.

[f] This parameter is defined in accordance with JEDEC standard 65.

[g] Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at the differential cross points.

[h] Measured at a differential output using a balun. DC/DC voltage supply as aggressor, ~490kHz switching frequency. Device power supply bypass as shown in example schematics.

Table 23. Typical Qn Output Amplitude,  $T_A = 25^\circ\text{C}^{[a]}$

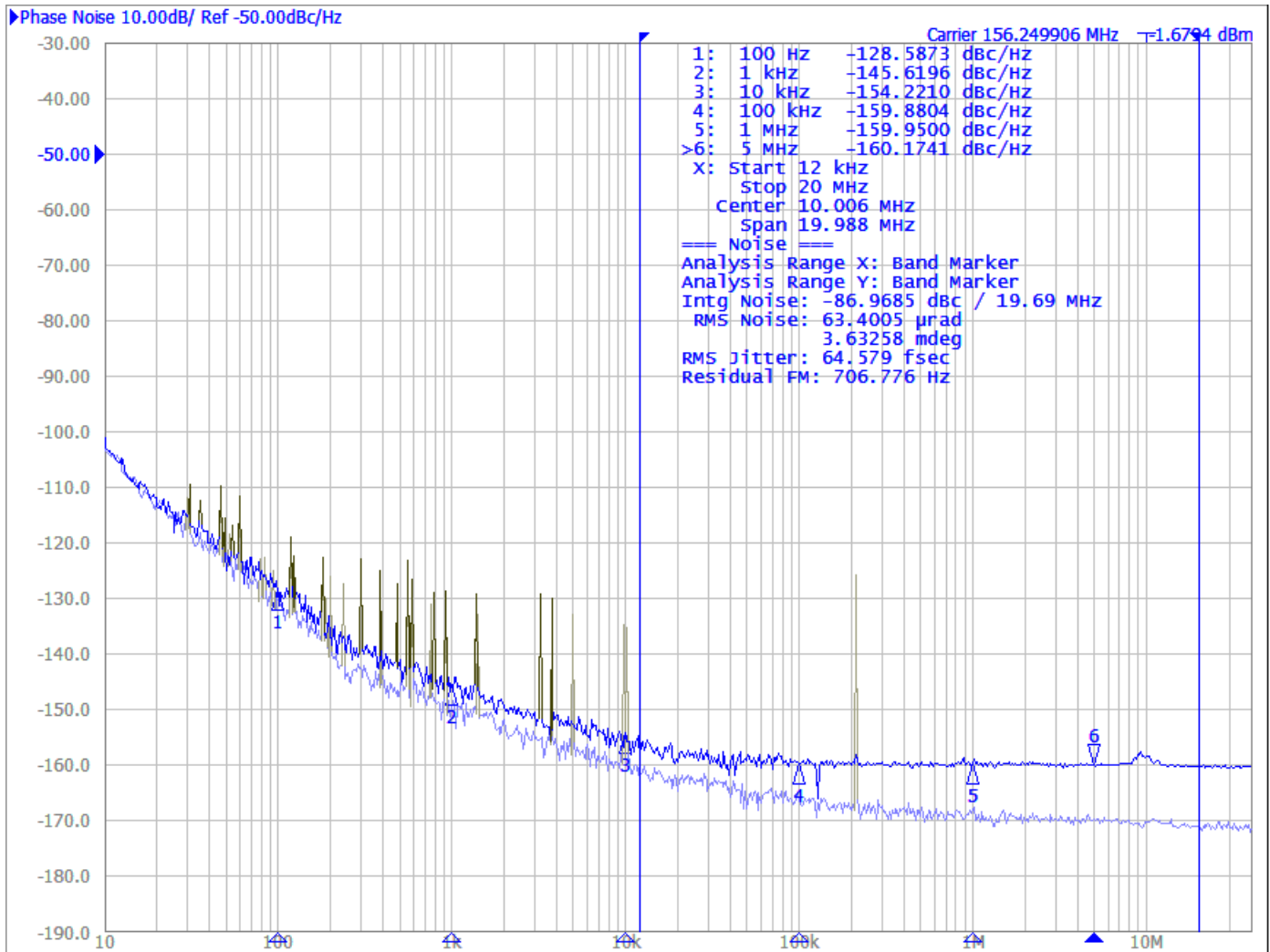
Symbol	Parameter	Test Conditions		Qn Output Frequency in MHz					Units
		Supply voltage	Output Amplitude	245.76	491.52	983.04	1966.08	2949.12	
$V_{O(PP)}^{[b]}$	LVPECL Output Voltage Swing, Peak-to-peak	$V_{DD\_V} = V_{DD\_O} = 3.3V$	500mV	540	490	499	499	351	mV
			750mV	783	710	722	720	506	mV
		$V_{DD\_V} = V_{DD\_O} = 2.5V$	500mV	538	494	499	518	376	mV
			750mV	773	705	717	732	530	mV
		$V_{DD\_V} = 2.5V$ $V_{DD\_O} = 1.8V$	500mV	523	481	489	505	373	mV

[a] Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfpm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

[b] LVPECL outputs terminated with  $50\Omega$  to  $V_{DD\_V} - 1.75V$  (500mV amplitude setting),  $V_{DD\_V} - 2.0V$  (750mV amplitude setting).

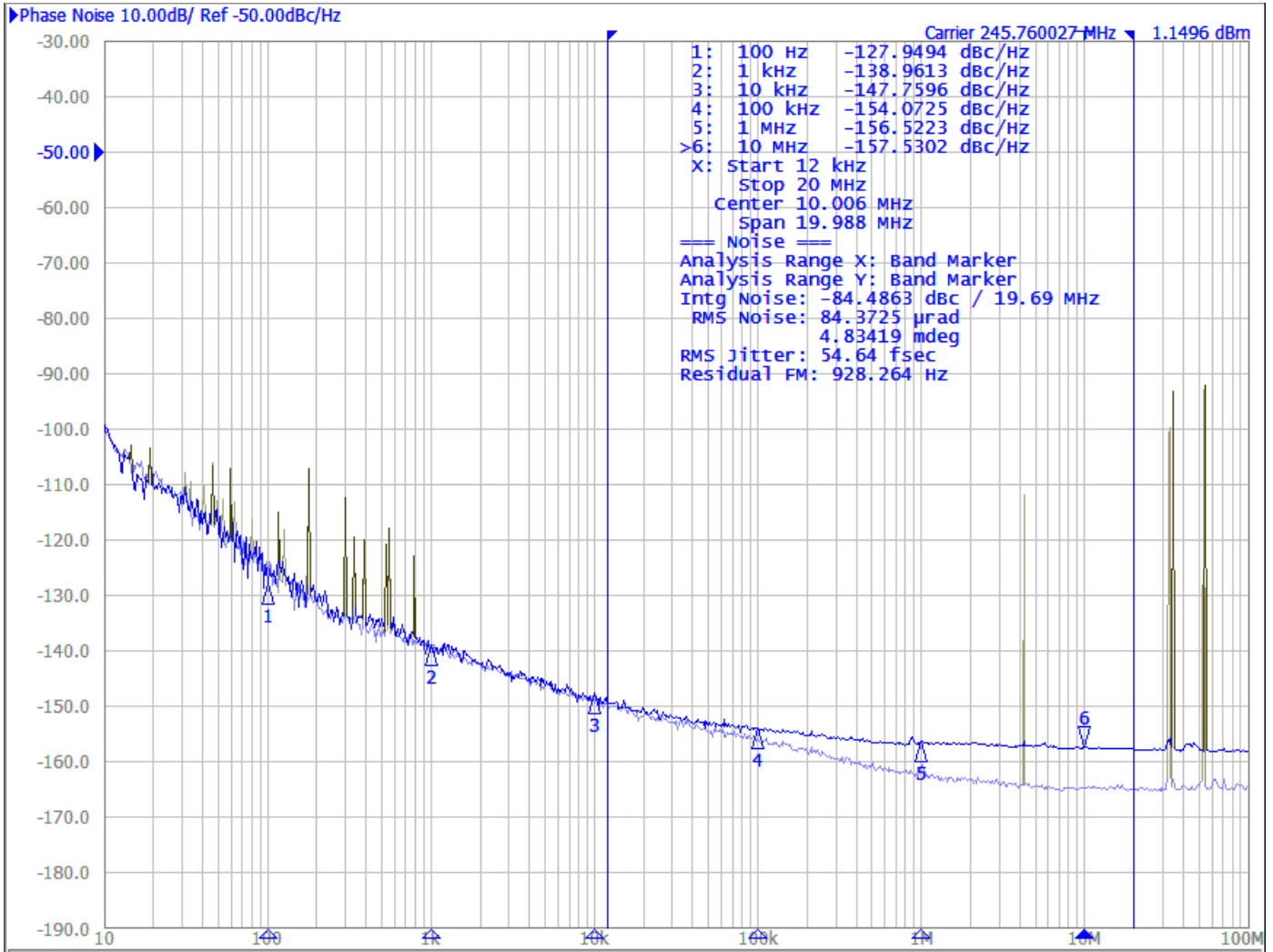
## Phase Noise Plots

Figure 4. Typical Phase Noise at 156.25MHz



\* Thick line: 8T79S308 output  
 Thin line: Wenzel oscillator drives 8T79S308 input

Figure 5. Typical Phase Noise at 245.76MHz

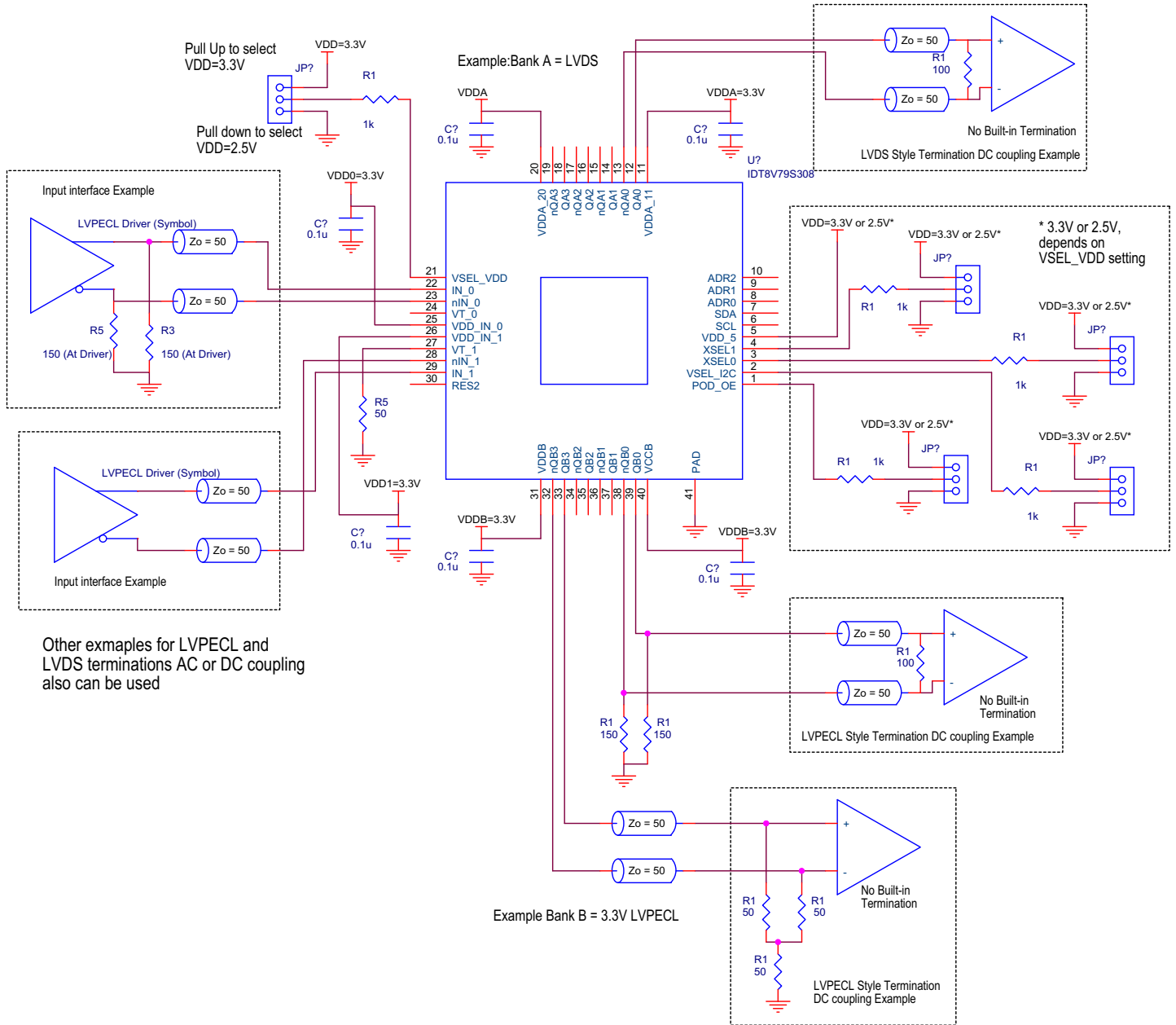


\* Thick line: 8T79S308 output  
 Thin line: Wenzel oscillator drives 8T79S308 input

# Application Information

The figure below shows an example schematics. Due to the excellent common-mode noise rejection characteristics, this device uses standard power supply bypass techniques and does not require dedicated, active power supply circuitry for noise rejection purpose.

Figure 6. Application Information

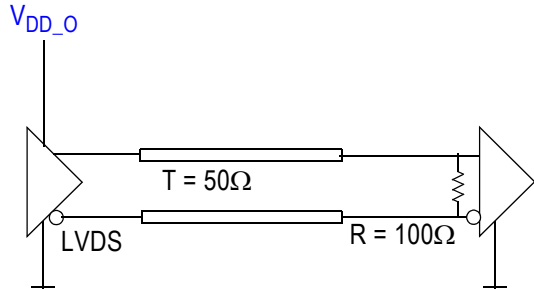


Other examples for LVPECL and LVDS terminations AC or DC coupling also can be used

## Termination for Q, nQ LVDS Outputs

Figure 7 shows an example termination for the Q, nQ LVDS outputs. In this example, the characteristic transmission line impedance is  $50\Omega$ . The termination resistor  $R$  ( $100\Omega$ ) is matched to the line impedance. The termination resistor must be placed at the line end. No external termination resistor is required if  $R$  is an internal part of the receiver circuit. The LVDS termination in Figure 7 is applicable for any output amplitude setting specified in Table 9.

Figure 7. LVDS Output Termination



## AC Termination for Q, nQ Outputs

Figure 8 and Figure 9 show example AC terminations for the Q, nQ LVDS outputs. In the examples, the characteristic transmission line impedance is  $50\Omega$ . In Figure 8, the termination resistor  $R$  ( $100\Omega$ ) is placed at the line end. No external termination resistor is required if  $R$  is an internal part of the receiver circuit, which is shown in Figure 9. The LVDS terminations in both Figure 8 and Figure 9 are applicable for any output amplitude setting specified in Table 9. The receiver input should be re-biased according to its common mode range specifications.

Figure 8. LVDS (STYLE = 0) AC Output Termination

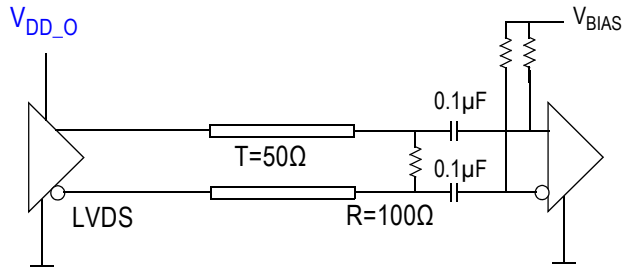
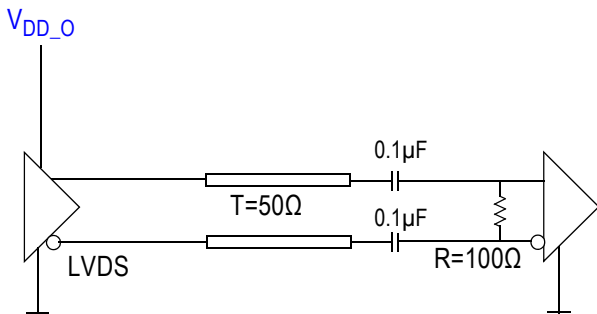


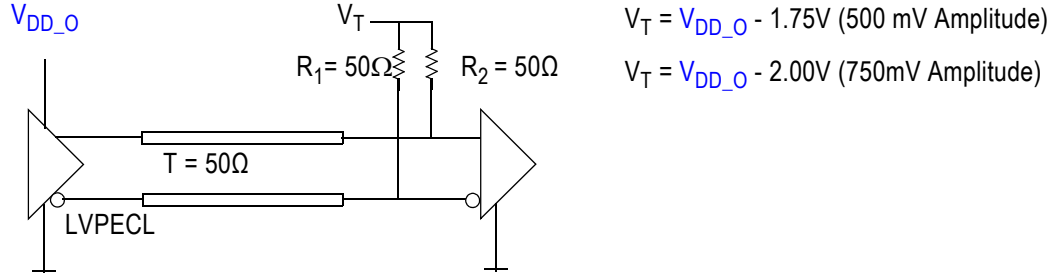
Figure 9. LVDS (STYLE = 0) AC Coupling



## Termination for Q, nQ LVPECL Outputs

Figure shows an example termination for the Q, nQ LVPECL outputs. In this example, the characteristic transmission line impedance is 50Ω. The R1 (50Ω) and R2 (50Ω) resistors are matched load terminations. The output is terminated to the termination voltage  $V_T$ .  $V_T$  must be set according to the output amplitude setting defined in Table 9. The termination resistors must be placed close at the line end.

Figure 10. Output Termination



## Termination for Q, nQ LVPECL Outputs AC-Coupled into HCSL-Receiver

Figure 11. LVPECL Output AC-Coupled into HCSL Receiver

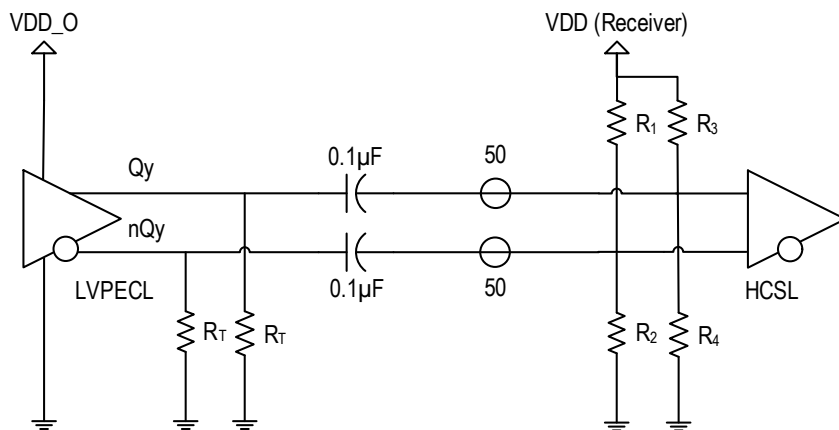


Table 24. Termination Resistors

	$V_{DD\_O} = 2.5V$	$V_{DD\_O} = 3.3V$
$R_T$	100Ω	180Ω

Table 25. HCSL Receiver Voltage Bias

	$V_{DD} = 2.5V$	$V_{DD} = 3.3V$
$R_1, R_3$	357Ω	470Ω
$R_2, R_4$	58Ω	56Ω

## Input Interface Circuits

Figure 12. LVDS Output Drives 8T79S308 Input (DC-Coupled)

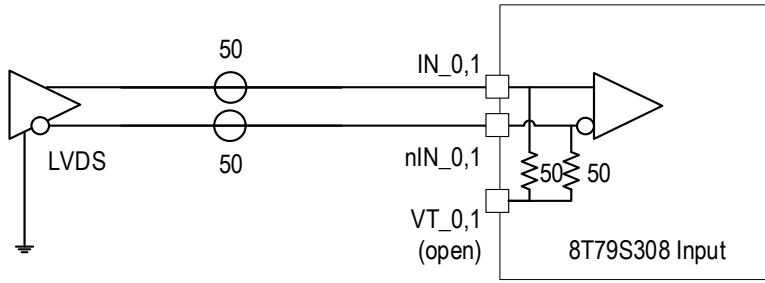
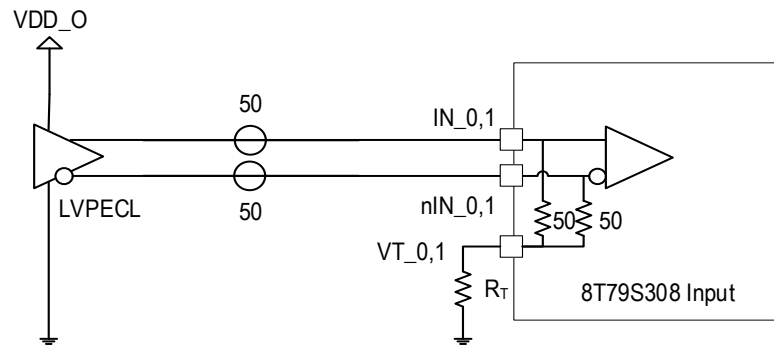
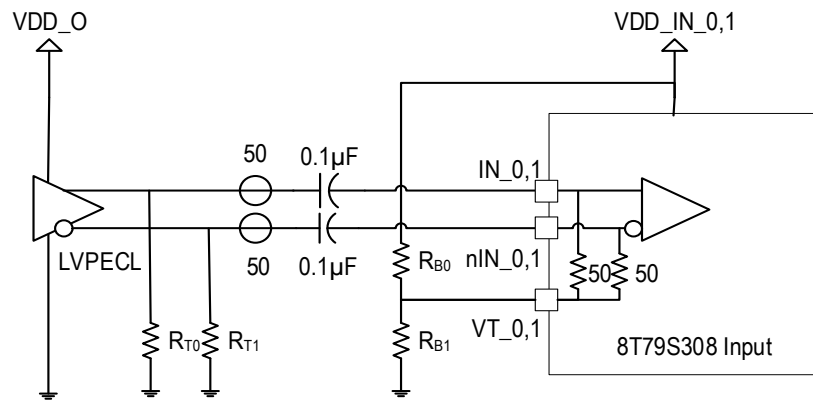


Figure 13. LVPECL Output Drives 8T79S308 Input (DC-Coupled)



	$V_{DD\_O} = 2.5V$	$V_{DD\_O} = 3.3V$
$R_T$	18Ω	50Ω

Figure 14. LVPECL Output Drives 8T79S308 Input (AC-Coupled)

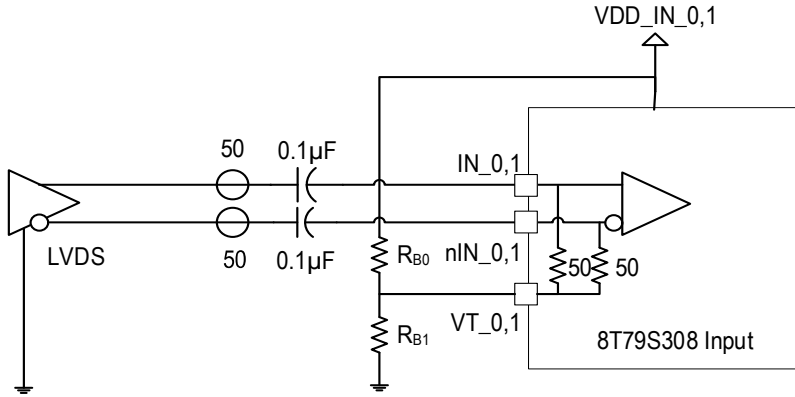


	$V_{DD\_O} = 2.5V$	$V_{DD\_O} = 3.3V$
$R_{T0,1}$	56Ω	120–240Ω

	$V_{DD\_IN0,1} = 2.5V$	$V_{DD\_IN0,1} = 3.3V$
$R_{B0}$	5.1kΩ	5.1kΩ
$R_{B1}$	10kΩ	10kΩ

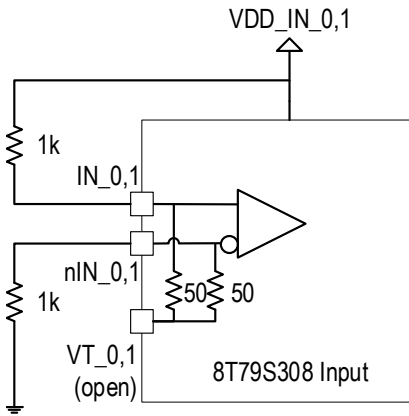


Figure 15. LVDS Output Drives 8T79S308 Input (AC-Coupled)



	$V_{DD\_IN0,1} = 2.5V$	$V_{DD\_IN0,1} = 3.3V$
$R_{B0}$	5.1k $\Omega$	5.1k $\Omega$
$R_{B1}$	10k $\Omega$	10k $\Omega$

Figure 16. Unused Input



## Thermal Characteristics

Table 26. Thermal Characteristics<sup>[a]</sup>

Multi-Layer PCB, JEDEC Standard Test Board				
Symbol	Thermal Parameter	Condition	Value	Unit
$\Theta_{JA}$	Junction to ambient	0 m/s air flow	24.6	°C/W
		1 m/s air flow	21.2	
		2 m/s air flow	19.6	
		3 m/s air flow	18.8	
		4 m/s air flow	18.2	
		5 m/s air flow	17.6	
$\Theta_{JC}$	Junction to case	—	21.6	
$\Theta_{JB}$	Junction to board <sup>[b]</sup>	—	1.2	

[a] Standard JEDEC 2S2P multilayer PCB.

[b] Thermal model where the heat dissipated in the component is conducted through the board.  $T_B$  is measured on or near the component lead.

## Temperature Considerations

The device supports applications in a natural convection environment as long as the junction temperature does not exceed the specified junction temperature  $T_J$ . In applications where the heat dissipates through the PCB,  $\Theta_{JB}$  is the correct metric to calculate the junction temperature.  $\Theta_{JB}$  is the right metric in all other applications where the majority of the heat dissipates through the board (80%) and a minority (20%) through the top of the device. The following calculation uses the junction-to-board thermal characterization parameter  $\Theta_{JB}$  to calculate the junction temperature ( $T_J$ ). Care must be taken to not exceed the maximum allowed junction temperature  $T_J$  of 125 °C.

The junction temperature  $T_J$  is calculated using the following equation:

$$T_J = T_B + P_{TOT} \times \Theta_{JB}$$

where:

- $T_J$  is the junction temperature at steady state conditions in °C
- $T_B$  is the board temperature at steady state condition in °C, measured on or near the component lead
- $\Theta_{JB}$  is the thermal characterization parameter to report the difference between  $T_J$  and  $T_B$
- $P_{TOT}$  is the total device power dissipation

**Application power dissipation scenarios:** Applications may use device settings that result in a lower power dissipation than the maximum power scenario. The device is a multi-functional, high-speed device that targets a variety of applications. Since this device is highly programmable with a broad range of settings and configurations, the power consumption will vary as settings and configurations are changed. [Table 27](#) and [Table 28](#) show the typical current consumption and total device power consumption along with the junction temperature for the four test cases shown in the tables. The tables also display the maximum board temperature for the  $\Theta_{JB}$  model.

Table 27. Typical Device Power Dissipation and Junction Temperature,  $V_{DD_V} = V_{DD_O} = 3.3V$

Test Case <sup>[a]</sup>	Output Configuration	Device		$\Theta_{JB}$ Thermal Model	
		$I_{DD\_TOT}$	$P_{TOT}$	$T_J$ <sup>[b]</sup>	$T_{B, MAX}$ <sup>[c]</sup>
		mA	W	°C	°C
1	Qn: LVPECL, 500mV	356	0.7174	105.87	124.13
2	Qn: LVPECL, 750mV	406	0.8142	105.98	124.02
3	Qn: LVDS, 350mV	300	0.99	106.19	123.81
4	Qn: LVDS, 500mV	308	1.02	106.23	123.77

[a] See [Table 21](#) and [Table 22](#) for device settings.

[b] Junction temperature at board temperature  $T_B=105^\circ\text{C}$ .

[c] Maximum board temperature for junction temperature  $<125^\circ\text{C}$ .

Table 28. Typical Device Power Dissipation and Junction Temperature,  $V_{DD_V} = V_{DD_O} = 2.5V$

Test Case <sup>[a]</sup>	Output Configuration	Device		$\Theta_{JB}$ Thermal Model	
		$I_{DD\_TOT}$	$P_{TOT}$	$T_J$ <sup>[b]</sup>	$T_{B, MAX}$ <sup>[c]</sup>
		mA	W	°C	°C
1	Qn: LVPECL, 500mV	346	0.585	105.71	124.29
2	Qn: LVPECL, 750mV	396	0.671	105.81	124.19
3	Qn: LVDS, 350mV	295	0.738	105.89	124.11
4	Qn: LVDS, 750mV	302	0.755	105.91	124.09

[a] See [Table 21](#) and [Table 22](#) for device settings.

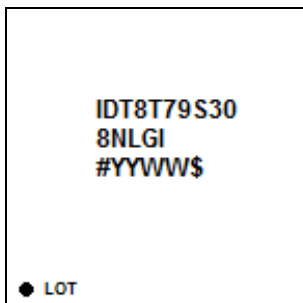
[b] Junction temperature at board temperature  $T_B=105^\circ\text{C}$ .

[c] Maximum board temperature for junction temperature  $<125^\circ\text{C}$ .

## Package Outline Drawings

The package outline drawings are located at the end of this document. The package information is the most current data available and is subject to change without notice or revision of this document.

## Marking Diagram



1. Lines 1 and 2 indicate the part number.
2. Line 3:
  - “#” denotes stepping.
  - “YY” is the last two digits of the year; “WW” is the work week number that the part was assembled.
  - “\$” denotes the mark code.

## Ordering Information

Orderable Part Number	Package	Shipping Packaging	Temperature
8T79S308NLGI	RoHS 6/6 40-VFQFPN, 6 × 6 mm	Tray	-40°C to +105°C
8T79S308NLGI8		Tape and Reel, Pin 1 Orientation: EIA-481-C	
8T79S308NLGI/W		Tape and Reel, Pin 1 Orientation: EIA-481-D/E	

Table 29. Pin 1 Orientation in Tape and Reel Packaging

Part Number Suffix	Pin 1 Orientation	Illustration
8	Quadrant 1 (EIA-481-C)	
/W	Quadrant 2 (EIA-481-D/E)	

## Glossary

Abbreviation	Description
Index $n$	Denominates a Q, nQ differential output and associated configuration bits. Range: A0, A1, A2, A4, B0, B1, B2, B3.
$V_{DD\_V}$	Denominates core voltage and input supply pins VDD, VDD_IN_0 and VDD_IN_1. Range: 3.3V, 2.5V.
$V_{DD\_O}$	Denominates output bank voltage pins VDDA and VDDDB. Range: 3.3V, 2.5V, 1.8V.
[...]	Index brackets describe a group associated with a logical function or a bank of outputs.
{...}	List of discrete values.

## Revision History

Revision Date	Description of Change
August 10, 2018	<ul style="list-style-type: none"> <li>▪ Updated the supported frequency range to “0 to 3GHz” in <a href="#">Features</a></li> <li>▪ Removed reference to “Design Target Specification” from all electrical characteristics tables</li> <li>▪ Added a footnote to <a href="#">Figure 4</a> and <a href="#">Figure 5</a></li> <li>▪ Completed other minor changes throughout</li> </ul>
May 31, 2018	Initial release.

## Notice

1. Descriptions of circuits, software and other related information in this document are provided only to illustrate the operation of semiconductor products and application examples. You are fully responsible for the incorporation or any other use of the circuits, software, and information in the design of your product or system. Renesas Electronics disclaims any and all liability for any losses and damages incurred by you or third parties arising from the use of these circuits, software, or information.
2. Renesas Electronics hereby expressly disclaims any warranties against and liability for infringement or any other claims involving patents, copyrights, or other intellectual property rights of third parties, by or arising from the use of Renesas Electronics products or technical information described in this document, including but not limited to, the product data, drawings, charts, programs, algorithms, and application examples.
3. No license, express, implied or otherwise, is granted hereby under any patents, copyrights or other intellectual property rights of Renesas Electronics or others.
4. You shall not alter, modify, copy, or reverse engineer any Renesas Electronics product, whether in whole or in part. Renesas Electronics disclaims any and all liability for any losses or damages incurred by you or third parties arising from such alteration, modification, copying or reverse engineering.
5. Renesas Electronics products are classified according to the following two quality grades: "Standard" and "High Quality". The intended applications for each Renesas Electronics product depends on the product's quality grade, as indicated below.
  - "Standard": Computers; office equipment; communications equipment; test and measurement equipment; audio and visual equipment; home electronic appliances; machine tools; personal electronic equipment; industrial robots; etc.
  - "High Quality": Transportation equipment (automobiles, trains, ships, etc.); traffic control (traffic lights); large-scale communication equipment; key financial terminal systems; safety control equipment; etc.Unless expressly designated as a high reliability product or a product for harsh environments in a Renesas Electronics data sheet or other Renesas Electronics document, Renesas Electronics products are not intended or authorized for use in products or systems that may pose a direct threat to human life or bodily injury (artificial life support devices or systems; surgical implantations; etc.), or may cause serious property damage (space system; undersea repeaters; nuclear power control systems; aircraft control systems; key plant systems; military equipment; etc.). Renesas Electronics disclaims any and all liability for any damages or losses incurred by you or any third parties arising from the use of any Renesas Electronics product that is inconsistent with any Renesas Electronics data sheet, user's manual or other Renesas Electronics document.
6. When using Renesas Electronics products, refer to the latest product information (data sheets, user's manuals, application notes, "General Notes for Handling and Using Semiconductor Devices" in the reliability handbook, etc.), and ensure that usage conditions are within the ranges specified by Renesas Electronics with respect to maximum ratings, operating power supply voltage range, heat dissipation characteristics, installation, etc. Renesas Electronics disclaims any and all liability for any malfunctions, failure or accident arising out of the use of Renesas Electronics products outside of such specified ranges.
7. Although Renesas Electronics endeavors to improve the quality and reliability of Renesas Electronics products, semiconductor products have specific characteristics, such as the occurrence of failure at a certain rate and malfunctions under certain use conditions. Unless designated as a high reliability product or a product for harsh environments in a Renesas Electronics data sheet or other Renesas Electronics document, Renesas Electronics products are not subject to radiation resistance design. You are responsible for implementing safety measures to guard against the possibility of bodily injury, injury or damage caused by fire, and/or danger to the public in the event of a failure or malfunction of Renesas Electronics products, such as safety design for hardware and software, including but not limited to redundancy, fire control and malfunction prevention, appropriate treatment for aging degradation or any other appropriate measures. Because the evaluation of microcomputer software alone is very difficult and impractical, you are responsible for evaluating the safety of the final products or systems manufactured by you.
8. Please contact a Renesas Electronics sales office for details as to environmental matters such as the environmental compatibility of each Renesas Electronics product. You are responsible for carefully and sufficiently investigating applicable laws and regulations that regulate the inclusion or use of controlled substances, including without limitation, the EU RoHS Directive, and using Renesas Electronics products in compliance with all these applicable laws and regulations. Renesas Electronics disclaims any and all liability for damages or losses occurring as a result of your noncompliance with applicable laws and regulations.
9. Renesas Electronics products and technologies shall not be used for or incorporated into any products or systems whose manufacture, use, or sale is prohibited under any applicable domestic or foreign laws or regulations. You shall comply with any applicable export control laws and regulations promulgated and administered by the governments of any countries asserting jurisdiction over the parties or transactions.
10. It is the responsibility of the buyer or distributor of Renesas Electronics products, or any other party who distributes, disposes of, or otherwise sells or transfers the product to a third party, to notify such third party in advance of the contents and conditions set forth in this document.
11. This document shall not be reprinted, reproduced or duplicated in any form, in whole or in part, without prior written consent of Renesas Electronics.
12. Please contact a Renesas Electronics sales office if you have any questions regarding the information contained in this document or Renesas Electronics products.

(Note1) "Renesas Electronics" as used in this document means Renesas Electronics Corporation and also includes its directly or indirectly controlled subsidiaries.

(Note2) "Renesas Electronics product(s)" means any product developed or manufactured by or for Renesas Electronics.

(Rev.4.0-1 November 2017)

## Corporate Headquarters

TOYOSU FORESIA, 3-2-24 Toyosu,  
Koto-ku, Tokyo 135-0061, Japan  
[www.renesas.com](http://www.renesas.com)

## Contact Information

For further information on a product, technology, the most up-to-date version of a document, or your nearest sales office, please visit:  
[www.renesas.com/contact/](http://www.renesas.com/contact/)

## Trademarks

Renesas and the Renesas logo are trademarks of Renesas Electronics Corporation. All trademarks and registered trademarks are the property of their respective owners.